

# Attachment A

L Number	Hits	Search Text	DB	Time stamp
1	29548	(magnetic near2 memory) or mram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:00
2	460792	(magnetic near2 memory) or mram or (thin near2 film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:01
3	161265	(data near line) or dataline or bitline or (bit near line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:03
4	1665741	array or cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:04
5	63197	read near2 (current or circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:05
6	99541	constant near2 current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:05
7	665516	amplifier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:06
8	9104	"atr" or "tmr"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:08
9	29548	((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:08
10	3232	((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film)) and ((data near line) or dataline or bitline or (bit near line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:08
11	2456	((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film)) and ((data near line) or dataline or bitline or (bit near line)) and (array or cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:09
12	812	((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film)) and ((data near line) or dataline or bitline or (bit near line)) and (array or cell) and (read near2 (current or circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:09
13	121	((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film)) and ((data near line) or dataline or bitline or (bit near line)) and (array or cell) and (read near2 (current or circuit)) and (constant near2 current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:09

14	101	(((((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film))) and ((data near line) or dataline or bitline or (bit near line))) and (array or cell)) and (read near2 (current or circuit))) and (constant near2 current)) and amplifier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:10
15	65	(((((magnetic near2 memory) or mram) and ((magnetic near2 memory) or mram or (thin near2 film))) and ((data near line) or dataline or bitline or (bit near line))) and (array or cell)) and (read near2 (current or circuit))) and (constant near2 current)) and amplifier) and ("atr" or "tmr")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/05 10:10